Preferred Device

Amplifier Transistors PNP Silicon

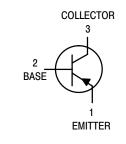
Features

• Pb-Free Packages are Available*



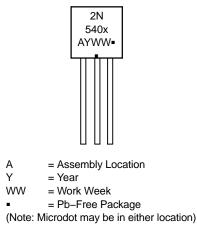
ON Semiconductor®

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MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS

Rating	Symbol	2N5400	2N5401	Unit
Collector – Emitter Voltage	V _{CEO}	120 150		Vdc
Collector – Base Voltage	V _{CBO}	130	160	Vdc
Emitter – Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	Ι _C	600		mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0		mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

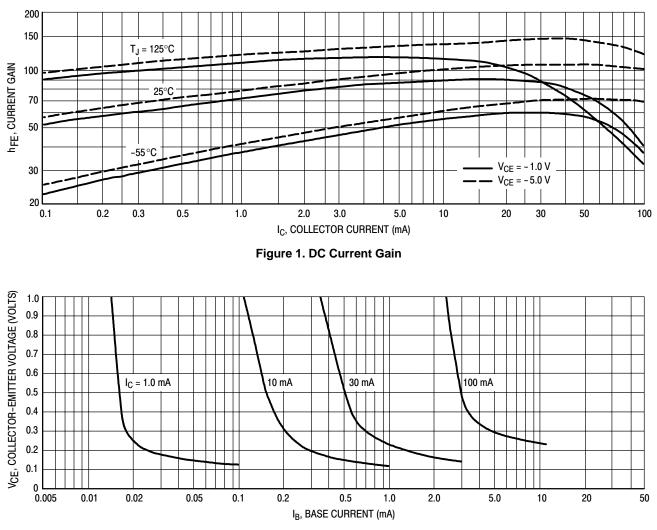
THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

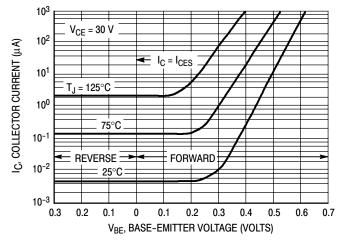
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
DFF CHARACTERISTICS		· · · · ·			
Collector-Emitter Breakdown Voltage ⁽¹⁾		V _{(BR)CEO}			Vdc
$(I_{C} = 1.0 \text{ mAdc}, I_{B} = 0)$	2N5400	()	120	-	
	2N5401		150	-	
Collector-Base Breakdown Voltage		V _{(BR)CBO}			Vdc
$(I_{\rm C} = 100 \mu {\rm Adc}, I_{\rm E} = 0)$	2N5400		130	_	
	2N5401		160	-	
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	5.0	_	Vdc
$(I_{E} = 10 \ \mu Adc, I_{C} = 0)$					
Collector Cutoff Current		I _{CBO}			
(V _{CB} = 100 Vdc, I _E = 0)	2N5400	020	_	100	nAdd
$(V_{CB} = 120 \text{ Vdc}, I_E = 0)$	2N5401		_	50	
$(V_{CB} = 100 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	2N5400		_	100	μAdc
$(V_{CB} = 120 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	2N5401		-	50	
Emitter Cutoff Current		I _{EBO}	_	50	nAdd
(V _{EB} = 3.0 Vdc, I _C = 0)					
DN CHARACTERISTICS (Note 1)					•
DC Current Gain		h _{FE}			_
(I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)	2N5400	. =	30	_	
	2N5401		50	-	
(I _C = 10 mAdc, V _{CE} = 5.0 Vdc)	2N5400		40	180	
(1C - 10 mAde, VCE - 3.0 Vde)	2N5400		40 60	240	
	2113401		00	240	
(I _C = 50 mAdc, V _{CE} = 5.0 Vdc)	2N5400		40	_	
	2N5401		50	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}			Vdc
$(I_{\rm C} = 10 \text{ mAdc}, I_{\rm B} = 1.0 \text{ mAdc})$		()	-	0.2	
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$			-	0.5	
Base-Emitter Saturation Voltage		V _{BE(sat)}			Vdc
$(I_{C} = 10 \text{ mAdc}, I_{B} = 1.0 \text{ mAdc})$		DE(out)	_	1.0	
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$			-	1.0	
SMALL-SIGNAL CHARACTERISTICS		· ·		•	
Current-Gain — Bandwidth Product		f _T			MHz
(I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	2N5400		100	400	
	2N5401		100	300	
Output Capacitance		C _{obo}	_	6.0	pF
$(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$					
Small–Signal Current Gain		h _{fe}		Ì	-
(I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N5400		30	200	
	2N5401		40	200	
Noise Figure		NF	_	8.0	dB
(I _C = 250 μAdc, V _{CE} = 5.0 Vdc, R _S = 1.0 kΩ, f = 1.0 kHz)				1	1

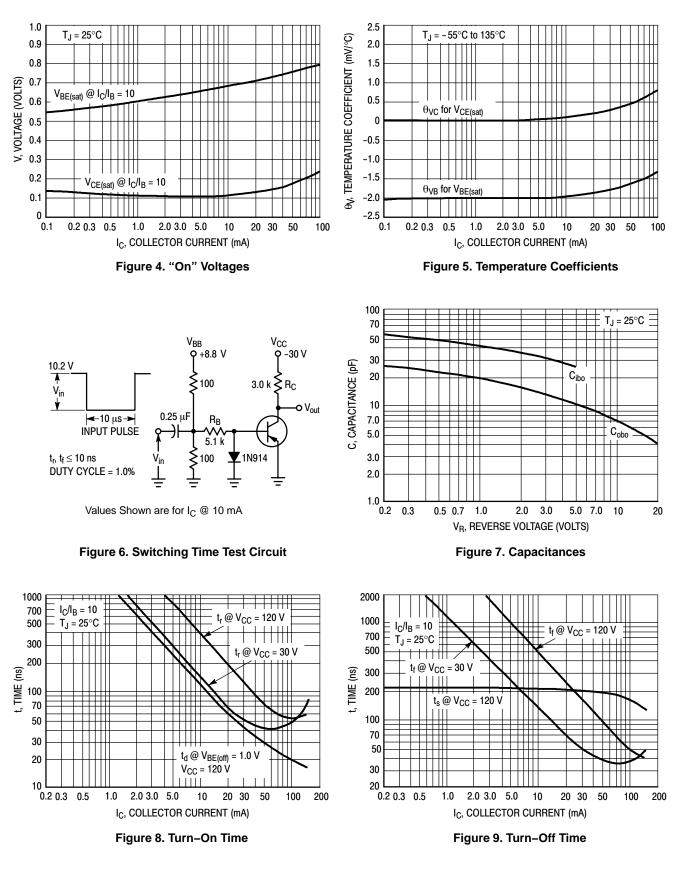
1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.











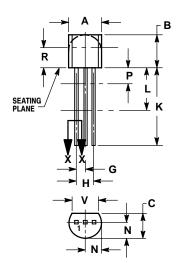
ORDERING INFORMATION

Device	Package	Shipping [†]		
2N5400	TO-92	5000 Unit / Bulk		
2N5400G	TO-92 (Pb-Free)	5000 Unit / Bulk		
2N5400RLRP	TO-92	2000 Tape & Reel		
2N5400RLRPG	TO-92 (Pb-Free)	2000 Tape & Reel		
2N5401	TO-92	5000 Unit / Bulk		
2N5401G	TO-92 (Pb-Free)	5000 Unit / Bulk		
2N5401RL1	TO-92	2000 Tape & Reel		
2N5401RL1G	TO-92 (Pb-Free)	2000 Tape & Reel		
2N5401RLRA	TO-92	2000 Tape & Reel		
2N5401RLRAG	TO–92 (Pb–Free)	2000 Tape & Reel		
2N5401RLRM	TO-92	2000 Tape & Ammo Box		
2N5401RLRMG	TO-92 (Pb-Free)	2000 Tape & Ammo Box		
2N5401ZL1	TO-92	2000 Tape & Ammo Box		
2N5401ZL1G	TO–92 (Pb–Free)	2000 Tape & Ammo Box		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 CASE 29-11 ISSUE AL





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH

2. CONTROLLING DIMENSION: INCH. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R

IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND DEVICED DIMENSION & MINIMUM

REAOND	DIMENSION	ĸ	MINIMU	JM.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
C	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR

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